Poster Presentation

## [PHp1]Phosphors and Devices

Thu. Nov 28, 2019 10:40 AM - 1:10 PM Main Hall (1F)

10:40 AM - 1:10 PM

## [PHp1-5L]Formation of ZnAl<sub>2</sub>O<sub>4</sub> Thin Film for Deep Ultraviolet Emitting Phosphor and Evaluation of Luminescence Properties

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 $ZnAl_2O_4$  thin films for deep UV emitting phosphor were prepared by thermal diffusion of ZnO and asapphire substrate at 1000 °C. From analysis of UV emission intensity by cathodoluminescence and penetration depth, it is considered that emiting layer of 650 nm was formed.